



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-123 Plastic-Encapsulate Diodes

BAV19W~BAV21W SWITCHING DIODE

FEATURES

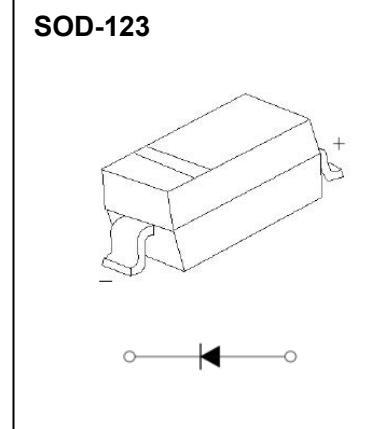
- Low Reverse Current
- Surface Mount Package Ideally Suited for Automatic Insertion
- Fast Switching Speed
- For General Purpose Switching Applications

MARKING:

BAV19W: A8

BAV20W: T2

BAV21W: T3



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value			Unit
		BAV19W	BAV20W	BAV21W	
V _{RM}	Non-Repetitive Peak Reverse Voltage	120	200	250	V
V _{RRM}	Peak Repetitive Reverse Voltage	100	150	200	V
V _{RWM}	Working Peak Reverse Voltage				
V _{R(RMS)}	RMS Reverse Voltage	71	106	141	V
I _o	Average Rectified Output Current	200			mA
I _{FSM}	Non-repetitive Peak Forward Surge Current @ t=8.3ms	1.7			A
P _D	Power Dissipation	500			mW
R _{θJA}	Thermal Resistance from Junction to Ambient	250			°C/W
T _j	Junction Temperature	150			°C
T _{stg}	Storage Temperature	-55~+150			°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Typ	Max	Unit
Reverse current	I _R	V _R =100V	BAV19W			0.1	uA
		V _R =150V	BAV20W			0.1	
		V _R =200V	BAV21W			0.1	
Forward voltage	V _F	I _F =100mA				1	V
		I _F =200mA				1.25	
Total capacitance	C _{tot}	V _R =0V,f=1MHz				5	pF
Reverse recovery time	t _{rr}	I _F = I _R =30mA, I _r =0.1*I _R , R _L =100Ω				50	ns

Typical Characteristics

BAV19W

